

M54HC4051/52/53 M74HC4051/52/53

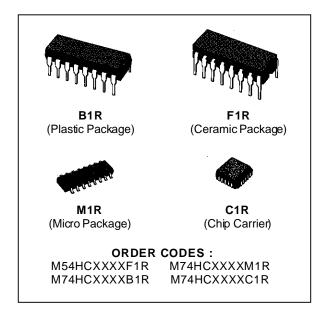
ANALOG MULTIPLEXER/DEMULTIPLEXER: SINGLE 8 CHANNEL, DUAL 4 CHANNEL, TRIPLE 2 CHANNEL

- LOW POWER DISSIPATION $I_{CC} = 4 \mu A \text{ (MAX.)} AT T_A = 25 \, ^{\circ}\text{C}$
- LOGIC LEVEL TRANSLATION TO ENABLE 5V LOGIC SIGNAL TO COMMUNICATE WITH ±5V ANALOG SIGNAL
- LOW "ON" RESISTANCE: 70Ω TYP. (V_{CC} - V_{EE} = 4.5 V) 50Ω TYP. (V_{CC} - V_{EE} = 9 V)
- WIDE ANALOG INPUT VOLTAGE RANGE: ±6V
- FAST SWITCHING: tpd = 15 ns (TYP.) AT T_A = 25 °C
- LOW CROSSTALK BETWEEN SWITCHES
- HIGH ON/OFF OUTPUT VOLTAGE RATIO
- WIDE OPERATING VOLTAGE RANGE (Vcc - Vee) = 2V TO 12V
- LOW SINE WAVE DISTORTION 0.02% AT V_{CC} - V_{EE} = 9V
- HIGH NOISE IMMUNITY

 VNIH = VNIL = 28 % VCC (MIN.)
- PIN AND FUNCTION COMPATIBLE WITH HCC/HCF4051/4052/4053B

DESCRIPTION

These devices are analog multiplexer demultiplexers in high speed silicon gate C²MOS technology and they are pin compatible with the equivalent metal gate CMOS "4000B" series. These analog switches are bidirectional and digitally

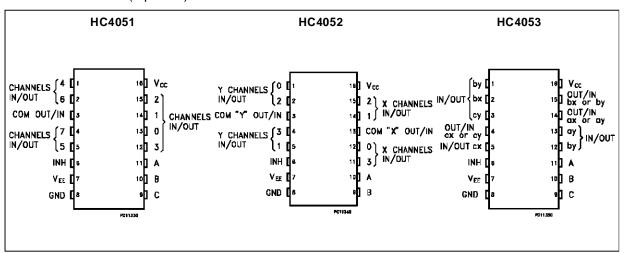


controlled.

A built-in level shifting is included to allow them an input range of up to \pm 6V (peak) for an analog signal with digital control signal of 0 to 6V.

VEE supply pin is provided for analog input signals. They have an inhibit (INH) input terminal to disable all the switches when high. For operation as a digital multiplexer/demultiplexer, VEE is connected to GND.

PIN CONNECTION (top view)



October 1993 1/15

DESCRIPTION

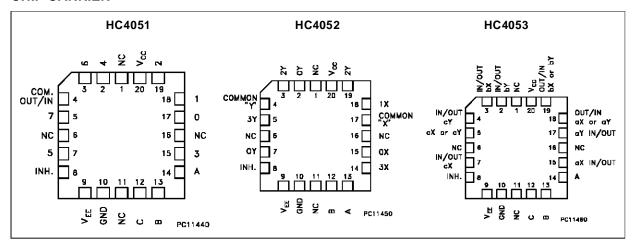
The HC4051 is a single 8 channel multiplexer demultiplexer having three binary control inputs A, B and C to select 1 of 8 to be turned on, and connected to the output.

The HC4052 has a pair of four channel multiplexer demultiplexer having two control inputs A and B that

select one of four channels of the two sections.

The HC4053 is a triple two channel multiplexer demultiplexer having three separate digital control inputs A, B and C to select independently one of a pair of channles.

CHIP CARRIER



TRUTH TABLE (HC4051)

INPL	JT STA	TES		"ON" CHANNEL
INHIBIT	С	В	Α	ON CHANNEL
L	L	Ш	L	0
L	L	Ш	Н	1
L	L	Η	L	2
L	L	Η	Н	3
L	Н	Ш	L	4
L	Н	Ш	Н	5
L	Н	Τ	L	6
L	Н	Н	Н	7
Н	Χ	Χ	Χ	NONE

X: DON'T CARE

TRUTH TABLE (HC4052)

INPUT S	STATES	"ON" CHANNELS	
INHIBIT	В	Α	ON CHANNELS
L	L	L	0X, 0Y
L	L	Ι	1X, 1Y
L	Н	L	2X, 2Y
L	Н	Н	3X, 3Y
Н	Х	Х	NONE

X: DON'T CARE

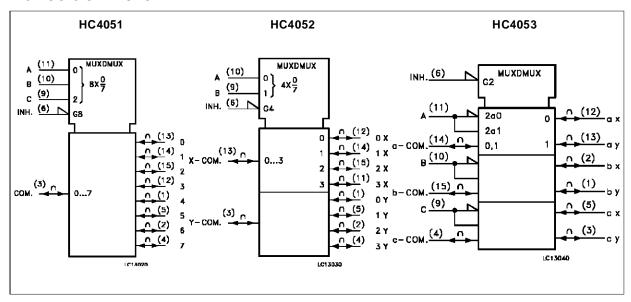
TRUTH TABLE (HC4053)

INPUT	STATES	"ON" CHANNELS
INHIBIT	A or B or C	ON CHANNELS
L	L	ax or bx or cx
L	Н	ay or by or cy
Н	Х	NONE

X: DON'T CARE



IEC LOGIC SYMBOLS



PIN DESCRIPTION (HC4051)

PIN No	SYMBOL	NAME AND FUNCTION
3	COM	Common Output/input
	OUT/IN	
6	INH	INHIBIT Input
7	V_{EE}	Negative Supply Voltage
11, 10, 9	A, B, C	Select Inputs
13, 14, 15,	0 TO 7	Independent Input/Outputs
12, 1, 5, 2, 4		
8	GND	Ground (0V)
16	Vcc	Positive Supply Voltage

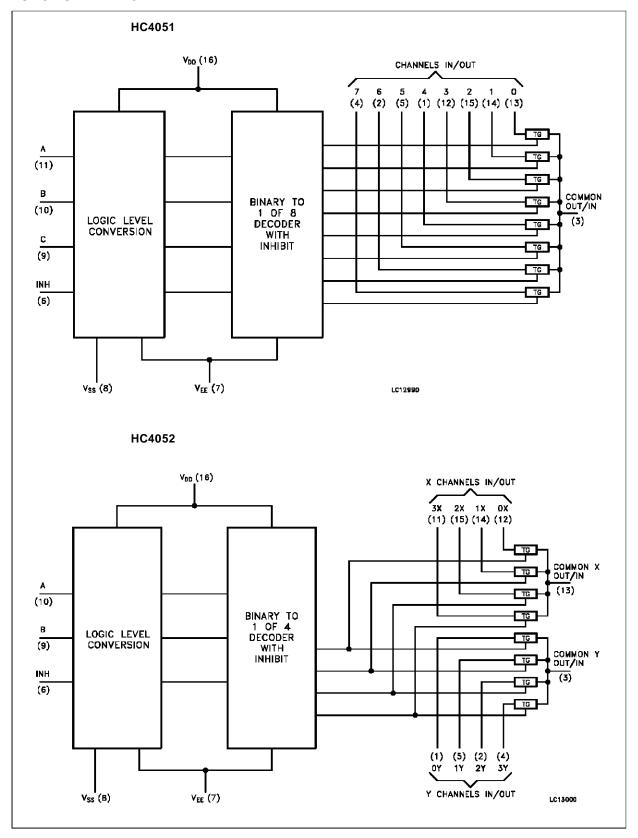
PIN DESCRIPTION (HC4053)

PIN No	SYMBOL	NAME AND FUNCTION
2, 1	bx, by	Independent Input/Outputs
5, 3	cx, cy	Independent Input/Outputs
6	INH	INHIBIT Input
7	V _{EE}	Negative Supply Voltage
11, 10, 9	A, B, C	Select Inputs
12, 13	ax, ay	Independent Input/Outputs
14, 15, 4	ax TO cy	Common Output/input
8	GND	Ground (0V)
16	Vcc	Positive Supply Voltage

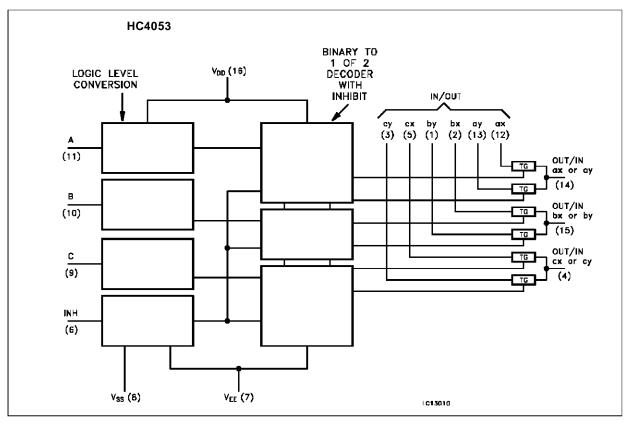
PIN DESCRIPTION (HC4052)

PIN No	SYMBOL	NAME AND FUNCTION
1, 5, 2, 4	0Y TO 3Y	Independent Input/Outputs
6	INH	INHIBIT Input
7	VEE	Negative Supply Voltage
10, 9	A, B	Select Inputs
12, 14, 15, 11	0X TO 3X	Independent Input/Outputs
3	COM Y OUT/IN	Common X Output/input
13	COM X OUT/IN	Common Y Output/input
8	GND	Ground (0V)
16	Vcc	Positive Supply Voltage

FUNCTIONAL DIAGRAM



FUNCTIONAL DIAGRAM



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
Vcc	Supply Voltage Range	-0.5 to +7	V
V _{CC} - V _{EE}	Supply Voltage Range	-0.5 to 13	V
V _{IN}	Control Input Voltage	-0.5 to V _{CC} + 0.5	V
V _{I/O}	Switch I/O Voltage	V _{EE} - 0.5 to V _{CC} + 0.5	V
Ick	Control Input Diode Current	± 20	mA
liok	I/O Diode Current	± 20	mA
ΙΤ	Switch Through Current	± 25	mA
Icc	DC V _{CC} or Ground Current	± 50	mA
P_{D}	Power Dissipation	500 (*)	mW
T _{stg}	Storage Temperature	-65 to +150	°C
TL	Lead Temperature (10 sec)	300	°C

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these conditions is not implied. (*) 500 mW: \cong 65 °C derate to 300 mW by 10mW/°C: 65 °C to 85 °C

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter		Value	Unit
Vcc	Supply Voltage		2 to 6	V
V _{EE}	Supply Voltage		-6 to 0	V
V _{CC} - V _{EE}	Supply Voltage		2 to 12	V
V _{IN}	Input Voltage		0 to V _{CC}	V
V _{I/O}	Input/Output Voltage		V _{EE} to V _{CC}	V
Тор	Operating Temperature: M54HC Series M74HC Series		-55 to +125 -40 to +85	°C
t _r , t _f	Input Rise and Fall Time	V _{CC} = 2 V	0 to 1000	ns
		V _{CC} = 4.5 V	0 to 500	
		V _{CC} = 6 V	0 to 400	

DC SPECIFICATIONS

		Test Conditions				Value						
Symbol Parameter		V cc (V)	V _{EE}			_A = 25 ^o C and 7			85 °C HC		125 °C HC	Unit
		(٧)	(۷)		Min.	Тур.	Max.	Min.	Max.	Min.	Max.	
ViHC	High Level	2.0			1.5			1.5		1.5		
	Control Input	4.5			3.15			3.15		3.15		V
	Voltage	6.0			4.2			4.2		4.2		
VILC	Low Level	2.0					0.5		0.5		0.5	
	Control Input	4.5					1.35		1.35		1.35	V
	Voltage	6.0					1.8		1.8		1.8	
Ron	ON Resistance	4.5	GND	V _{IN} = V _{IHC} or V _{ILC}		85	180		225		270	
		4.5	-4.5	$V_{I/O} = V_{CC}$ to V_{EE}		55	120		150		180	
		6.0	-6.0	I _{I/O} ≤ 2 mA		50	100		125		150	
		2.0	GND	$ \begin{array}{c} V_{IN} = V_{IHC} \ or \ V_{ILC} \\ V_{I/O} = V_{CC} \ or \ V_{EE} \\ I_{I/O} \leq 2 \ mA \end{array} $		150						Ω
		4.5	GND			70	150		190		230	
		4.5	-4.5			50	100		125		150	
		6.0	-6.0			45	80		100		120	
ΔR_{ON}	Difference of	4.5	GND	V _{IN} = V _{IHC} or V _{ILC}		10	30		35		45	
	ON Resistance	4.5	-4.5	$V_{I/O} = V_{I/C}$ or V_{EE}		5	12		15		18	Ω
	Between Switches	6.0	-6.0	I _{I/O} ≤ 2 mA		5	10		12		15	
loff	Input/Output	6.0	GND	Vos = Vcc or			±0.06		±0.6		±1.2	
	Leakage Current (SWITCH OFF)	6.0	-6.0	$ \begin{aligned} & \text{GND} \\ & \text{V}_{\text{IS}} = \text{GND or V}_{\text{CC}} \\ & \text{V}_{\text{IN}} = \text{V}_{\text{ILC}} \text{ or V}_{\text{IHC}} \end{aligned} $			±0.1		±1		±2	μА
I _{IZ}	Switch Input	6.0	GND	$V_{OS} = V_{CC}$ or			±0.06		±0.6		±1.2	
	Leakage Current (SWITCH ON, OUTPUT OPEN)	6.0		GND V _{IN} = V _{IHC} or V _{ILC}			±0.1		±1		±2	μΑ
I _{IN}	Control Input Current	6.0	GND	$V_{IN} = V_{CC}$ or GND			±0.1		±0.1		±1	μΑ
Icc	Quiescent	6.0	GND	V _{IN} = V _{CC} or GND			4		40		80	μΑ
	Supply Current	6.0	-6.0	VIN - VCC OI GIND			8		80		160	



AC ELECTRICAL CHARACTERISTICS ($C_L = 50 \text{ pF}$, Input $t_r = t_f = 6 \text{ ns}$)

		Te	est Co	nditions	Value							
Symbol	Parameter	Vcc Vee		54		$T_A = 25$ °C 54HC and 74HC			85 °C HC		125 °C HC	Unit
		(V)	(V)		Min.	Тур.	Max.	Min.	Max.	Min.	Max.	
$\Phi_{\text{I/O}}$	Phase Difference	2.0	GND			25	60		75		90	
	Between Input	4.5	GND			6	12		15		18	ns
	and Output	6.0	GND			5	10		13		15	
		4.5	-4.5			4						
t _{PZL}	Output Enable	2.0	GND	$R_L = 1K\Omega$		64	225		280		340	
tpzh	Time	4.5	GND			18	45		56		68	ns
	(for 4051/4052)	6.0	GND			15	38		48		58	
		4.5	-4.5			18						
t_{PZL}	Output Enable	2.0	GND	$R_L = 1K\Omega$		50	225		280		340	
t _{PZH}	Time	4.5	GND			14	45		56		68	ns
	(for 4053)	6.0	GND			12	38		48		58	
		4.5	-4.5			14						
t _{PLZ}	Output Disable	2.0	GND	$R_L = 1K\Omega$		100	250		315		375	
t _{PHZ}	Time	4.5	GND			33	50		63		7	ns
	(for 4051/4052)	6.0	GND			28	43		54		64	
		4.5	-4.5			29						
tplz	Output Disable	2.0	GND	$R_L = 1K\Omega$		95	225		280		340	
t _{PHZ}	Time	4.5	GND			30	45		56		68	ns
	(for 4053)	6.0	GND			26	38		48		58	
		4.5	-4.5			26						
C _{IN}	Input Capacitance					5	10		10		10	pF
C _{I/O}	Common Terminal			HC4051		36	70		70		70	
	Capacitance	5.0	-5.0	HC4052		19	40		40		40	pF
	0 ' 1 T ' 1			HC4053		11	20		20	-	20	
C _{I/O}	Switch Terminal Capacitance	5.0	-5.0	HC4051 HC4052		7 7	15 15		15 15		15 15	pF
	Capacitance	3.0	-3.0	HC4053		7	15		15		15	ρı
C _{IOS}	Feed Through			HC4051		0.95	2		2		2	
00	Capacitance	5.0	-5.0	HC4052		0.85	2		2		2	pF
				HC4053		0.75	2		2		2	
C _{PD} (*)	Power Dissipation	5.0	GND	HC4051		70 71						<u> </u>
	Capacitance			HC4052 HC4053		71 67						pF

^(*) C_{PD} is defined as the value of the IC's internal equivalent capacitance which is calculated from the operating current consumption without load. (Refer to Test Circuit). Average operating current can be obtained by the following equation. $I_{CC}(opr) = C_{PD} \bullet V_{CC} \bullet f_{IN} + I_{CC}$

ANALOG SWITCH CHARACTERISTICS (GND = $0 \text{ V T}_A = 25 \text{ }^{\circ}\text{C}$)

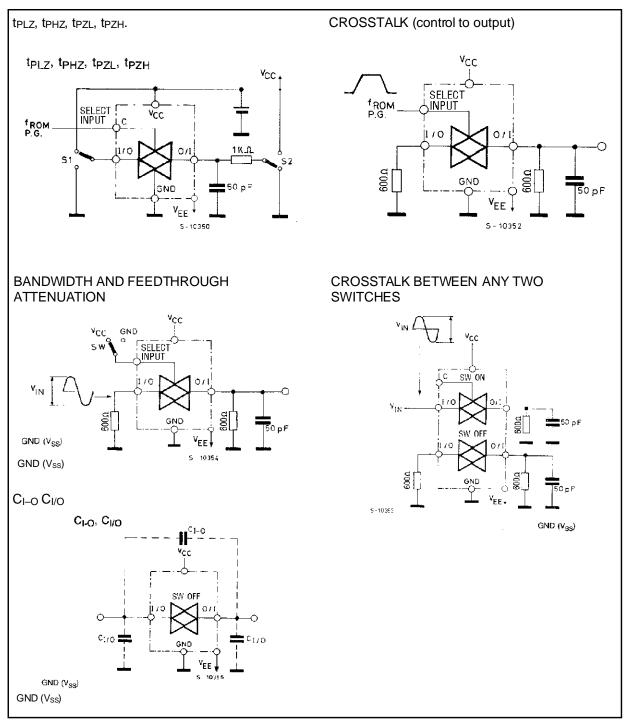
		Test Conditions						
Symbol	Parameter	V _{CC}	V _{EE}	VIN (Vp-p)			Тур.	Unit
	Sine Wave	2.25	2.25	4		L = 50 pF	0.025	
	Distortion	4.5	-4.5	8			0.020	%
		6.0	-6.0	11			0.018	
f_{MAX}	Frequency				f _{IN} voltage to Obtain 0 dBm at V _{OS} .	ALL (*)	120	
	Response (Switch ON)	2.25	-2.25		ease f_{IN} Frequency until dB Meter Reads -3dB 50 Ω C _L = 10 pF f_{IN} = 1 KHz	HC4051 (**) HC4052 (**) HC4053 (**)	45 70 95	
		4.5	-4.5		sine wave	ALL (*)	190	
						HC4051 (**) HC4052 (**) HC4053 (**)	70 110 150	MHz
		6.0	-6.0			ALL (*)	200	
						HC4051 (**) HC4052 (**) HC4053 (**)	85 140 190	
	Feedthrough	2.25	-2.25		V _{IN} is centered at (V _{CC} - V _{EE})/2		-50	
	Attenuation (2)	4.5	-4.5		Adjust input for 0 dBm		-50	dB
	(Switch OFF)	6.0	-6.0	K _L =	= 600Ω $C_L = 50 pF$ $f_{IN} = 1 KHz$	sine wave	-50	
	Crosstalk	2.25	-2.25		Adjust RL at set up so that $I_S = 0$	0A	60	
	(Control Input to	4.5	-4.5		$R_L = 600 \Omega$ $C_L = 50 pF$		140	mV
	Signal Output)	6.0	-6.0		f _{IN} = 1 MHz square wave		200	
	Crosstalk	2.25	-2.25		Adjust V _{IN} to Obtain 0 dBm at Inp		-50	
	(Between Any Switches)	4.5	-4.5	K _L =	$=600 \Omega$ $C_L = 50 pF$ $f_{IN} = 1 MHz$	sine wave	-50	dB
	Owntones)	6.0	-6.0				-50	

^{(*):} Input COMMON Terminal, and measured at SWITCH Terminal.

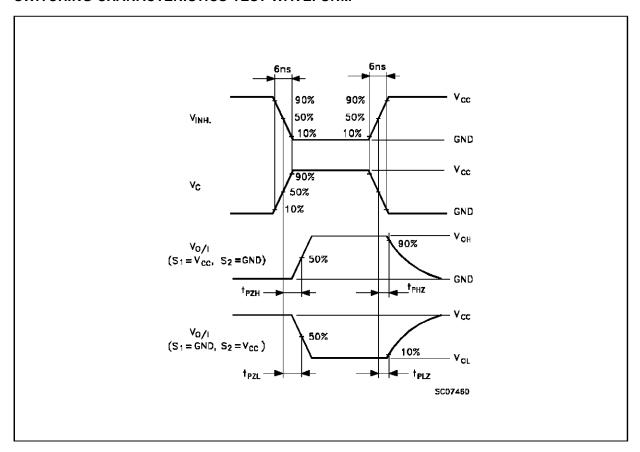
 $^{(\}ensuremath{^{\star\star}})$: Input SWITCH Terminal, and measured at COMMON Terminal.

NOTE: These characteristics are determined by design of devices.

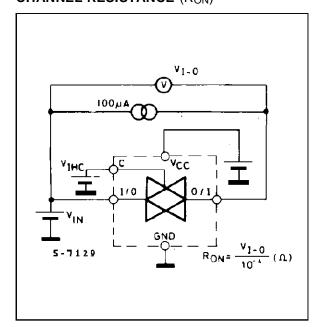
SWITCHING CHARACTERISTICS TEST CIRCUIT



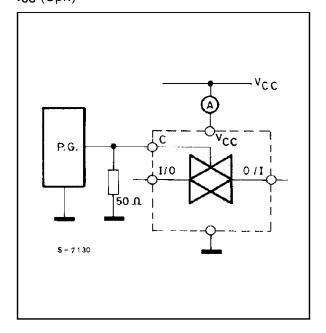
SWITCHING CHARACTERISTICS TEST WAVEFORM



CHANNEL RESISTANCE (RON)

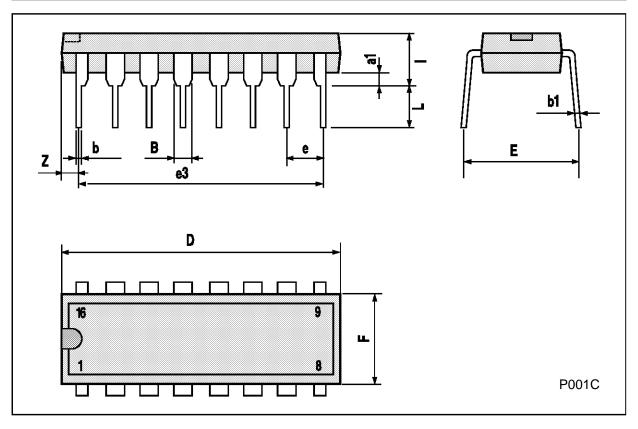


Icc (Opr.)



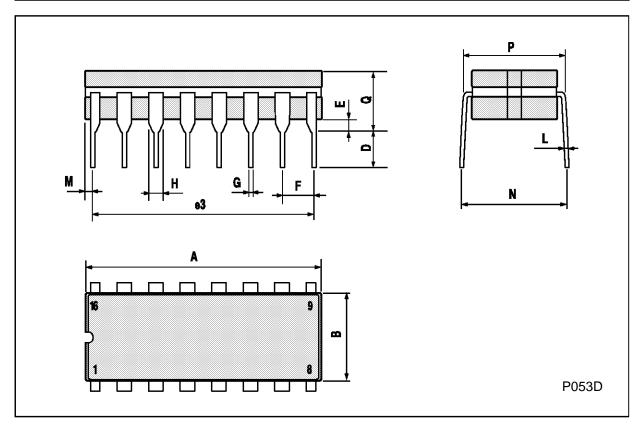
Plastic DIP16 (0.25) MECHANICAL DATA

DIM.		mm			inch	
Diwi.	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
a1	0.51			0.020		
В	0.77		1.65	0.030		0.065
b		0.5			0.020	
b1		0.25			0.010	
D			20			0.787
E		8.5			0.335	
е		2.54			0.100	
e3		17.78			0.700	
F			7.1			0.280
ı			5.1			0.201
L		3.3			0.130	
Z			1.27			0.050



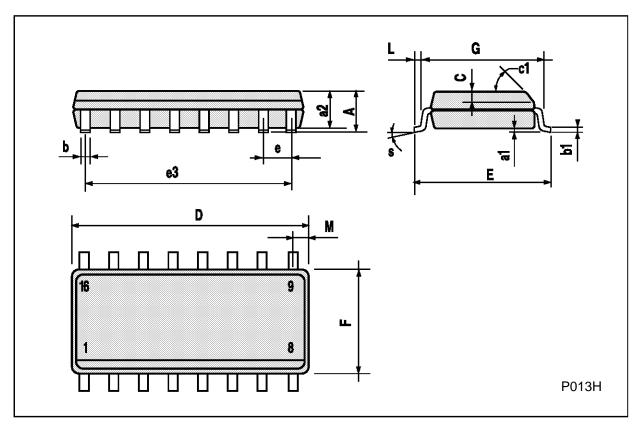
Ceramic DIP16/1 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
Α			20			0.787
В			7			0.276
D		3.3			0.130	
E	0.38			0.015		
e3		17.78			0.700	
F	2.29		2.79	0.090		0.110
G	0.4		0.55	0.016		0.022
Н	1.17		1.52	0.046		0.060
L	0.22		0.31	0.009		0.012
М	0.51		1.27	0.020		0.050
N			10.3			0.406
Р	7.8		8.05	0.307		0.317
Q			5.08			0.200



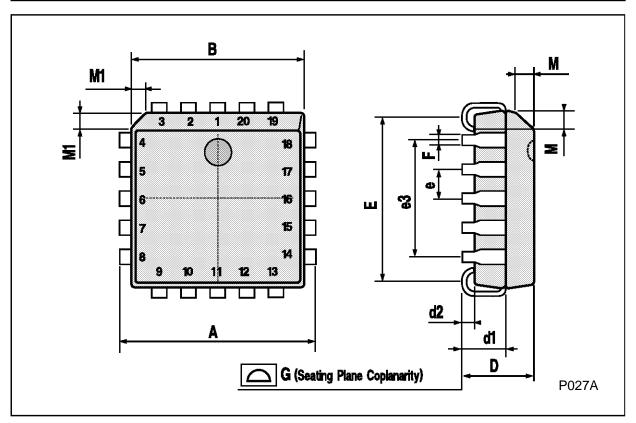
SO16 (Narrow) MECHANICAL DATA

DIM.	mm			inch				
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.		
Α			1.75			0.068		
a1	0.1		0.2	0.004		0.007		
a2			1.65			0.064		
b	0.35		0.46	0.013		0.018		
b1	0.19		0.25	0.007		0.010		
С		0.5			0.019			
c1	45° (typ.)							
D	9.8		10	0.385		0.393		
Е	5.8		6.2	0.228		0.244		
е		1.27			0.050			
e3		8.89			0.350			
F	3.8		4.0	0.149		0.157		
G	4.6		5.3	0.181		0.208		
L	0.5		1.27	0.019		0.050		
М			0.62			0.024		
S	8° (max.)							



PLCC20 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
Α	9.78		10.03	0.385		0.395
В	8.89		9.04	0.350		0.356
D	4.2		4.57	0.165		0.180
d1		2.54			0.100	
d2		0.56			0.022	
E	7.37		8.38	0.290		0.330
е		1.27			0.050	
e3		5.08			0.200	
F		0.38			0.015	
G			0.101			0.004
М		1.27			0.050	
M1		1.14			0.045	



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